

PRELIMINARY DATASHEET

600V 75A, N-Channel IGBT in Trench & Field Stop-technology in Isolated SOT227 Package

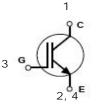
APPLICATIONS

- Uninterruptible power supplies (UPS)
- Solar inverters
- Welding inverters
- Motor drives
- Low power lighting: low frequency

FEATURES

- High speed switching
- Very low V_{CE(sat)}
- > Very tight parameter distribution
- > High ruggedness, temperature stable
- > Parallel switching capability
- > Very soft, fast recovery anti-parallel diode
- Pb-free finished; RoHS compliant

MAXIMUM RATINGS, at T_j = 25°C, unless otherwise specified





Parameter	Symbol	Value	Units
Collector-emitter voltage	V _{CE}	600	V
DC collector current, limited by T _{jmax} T _C = 25°C T _C = 80°C	lc	150 75	
Pulsed collector current, t_p limited by T_{jmax}	I _{Cpulse}	225	A
Turn off safe operating area $V_{CE} \leq 1200V, T_j \leq 150^{\circ}C$	-	225	
Gate-emitter voltage	V _{GE}	± 20	V
Short circuit withstand time ¹ $V_{GE} = 15V$, $V_{CC} \le 1200V$, $T_j \le 150^{\circ}C$	t _{sc}	5	μs
Soldering temperature Wave soldering, 1.6 mm (0.063 in.) from case for 10s	Ts	260	۰C
Operating junction and storage temperature	Tj, Tstg	-55 +175	°C

Thermal and Isolation Characteristics

Parameter	Symbol	Max. Value	Units
Characteristics			
IGBT thermal resistance, junction to case	R _{thJC}	0.46	K/W
Thermal resistance, junction to ambient	R _{thJA}	40	
Isolation voltage, RMS (measured between terminals and mounting base, 50-60 Hz, for 1-3 seconds)	Viso	3000	V

¹ Allowed number of short circuits: < 1000; time between short circuits: > 1s.

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ELECTRICAL CHARACTERISTICS, at $T_j = 25^{\circ}$ C, unless otherwise specified

Parameter	C	Conditions	Value			
	Symbol		Min.	Тур.	Max.	Unit
Static Characteristics						
Collector-emitter breakdown voltage	V _{(BR)CES}	$V_{GE} = 0V, I_C = 0.2 \text{ mA}$	600	-	-	
Collector-emitter saturation voltage	V _{CE(sat)}	$V_{GE} = 15V, I_C = 75A$ $T_j = 25^{\circ}C$ $T_j = 175^{\circ}C$	-	1.5 1.9	2.0	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_{C} = 1.2 \text{ mA}, V_{CE} = V_{GE}$	4.1	4.9	5.7	1
Zero gate voltage collector current	ICES	$V_{CE} = 600V, V_{GE} = 0$ $T_j = 25^{\circ}C$ $T_j = 175^{\circ}C$	-		40 1000	μA
Gate-emitter leakage current	IGES	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g fs	V _{CE} = 20V, I _C = 75A	-	41	-	S
Dynamic Characteristics						
Input capacitance	Ciss	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	4620	-	
Output capacitance	Coss		-	288	-	рF
Reverse transfer capacitance	Crss		-	137	-]
Gate charge	Q _{Gate}	V _{CC} = 480V, I _C = 75A V _{GE} = 15V	-	470	-	nC
Internal emitter inductance measured 5mm (0,197 in.) from case	LE		-	13	-	nH
Short circuit collector current ¹			-	687.5	_	A

SWITCHING CHARACTERISTICS, Inductive Load at $T_j = 25^{\circ}C$

Parameter	Symbol	Conditions	Value			11
			Min.	Тур.	Max.	Unit
Turn-on delay time	t _{d(on)}	T _j = 25∘C,	-	33	-	ns
Rise time	tr	V _{CC} =400V, I _C =75A, V _{GF} =0/15V,	-	36	-	
Turn-off delay time	t _{d(off)}	$R_G=5\Omega$, $L_{\sigma^2} = 100$ nH, $C_{\sigma^2} = 39$ pF Energy losses include tail and diode reverse recovery.	-	330	-	
Fall time	t _f		-	35	-	
Turn-on energy	Eon		-	2.0	-	mJ
Turn-off energy	E _{off}		-	2.5	-	
Total switching energy	Ets		-	4.5	-	

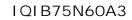
SWITCHING CHARACTERISTICS, Inductive Load at $T_j = 150$ °C

Parameter	S. mahal	Conditions	Value			11
	Symbol		Min.	Тур.	Max.	Unit
Turn-on delay time	t _{d(on)}		-	32	-	
Rise time	tr		-	37	-	ns
Turn-off delay time		T _j = 150°C,	-	363	-	
Fall time	t _f	V _{CC} =400V, I _C =75A, V _{GE} =0/15V,	-	38	-	
Turn-on energy	Eon	$R_G=5\Omega$,	-	2.9	-	
Turn-off energy	E _{off}		-	2.9	-	mJ
Total switching energy	Ets		-	5.8	-	1

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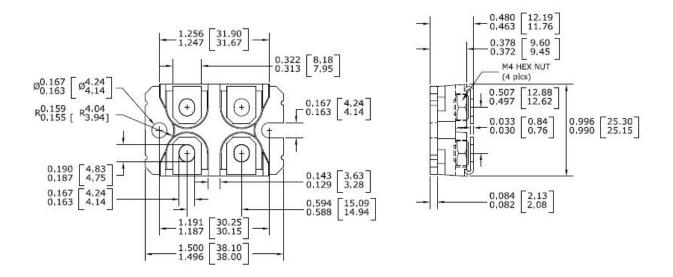
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Package Outline Drawing



CAUTION: These devices are ESD sensitive. Use proper handling procedure.

Disclaimer

These specifications may not be considered as a guarantee of components characteristics. Components have to be tested depending on intended application as adjustments may be necessary. The use of **iQXPRZ Power Inc.** components in life support appliances and systems are subject to written approval of **iQXPRZ Power Inc.**

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